

# SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# **ECH8664R** — General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance
- · 2.5V drive
- · Common-drain type
- · Protection diode in

- · Built-in gate protection resistor
- · Best suited for LiB charging and discharging switch
- · Halogen free compliance

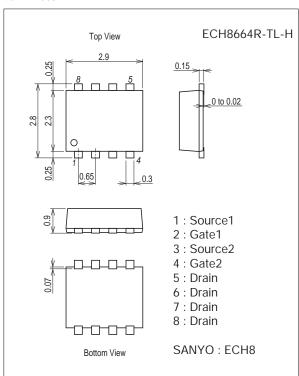
## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Drain Current (DC)	ID		7	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	1.3	W
Total Power Dissipation	PT	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7011A-003



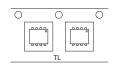
#### **Product & Package Information**

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

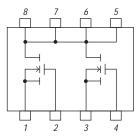
#### Packing Type: TL



#### Marking



#### **Electrical Connection**

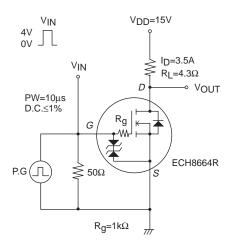


## ECH8664R

#### Electrical Characteristics at Ta=25°C

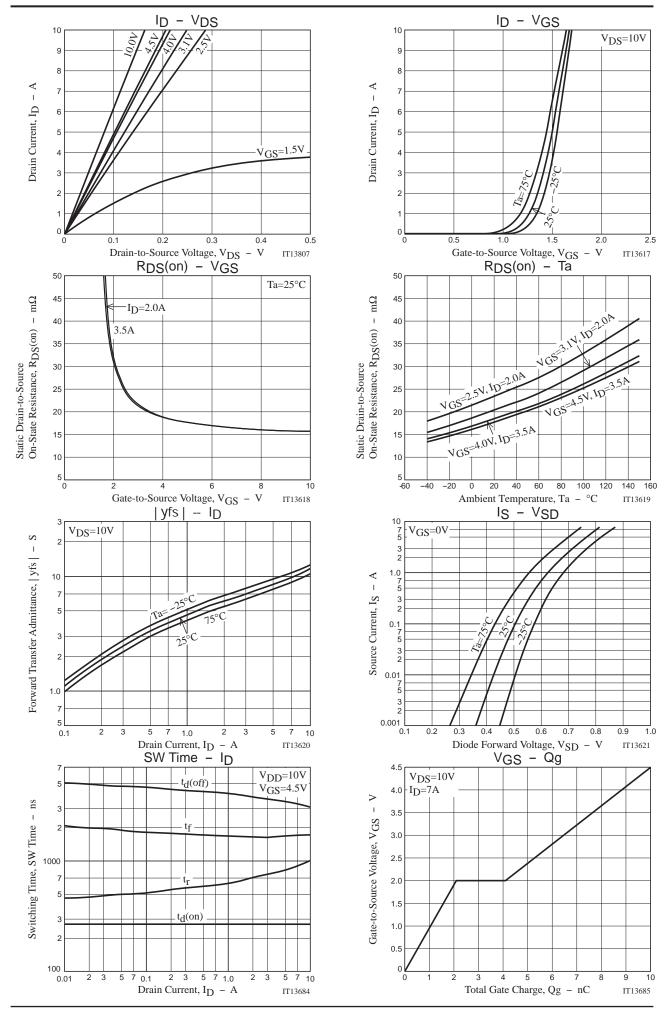
Parameter	Cymphol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.5		1.3	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A	4.5	7.5		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =3.5A, V <sub>G</sub> S=4.5V	12.5	18	23.5	mΩ	
Static Drain to Source On State Decistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =3.5A, V <sub>G</sub> S=4.0V	13	19	25	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =2A, V <sub>GS</sub> =3.1V	14.5	21	27.3	mΩ	
	RDS(on)4	ID=2A, VGS=2.5V	14.5	24	34	mΩ	
Turn-ON Delay Time	t <sub>d</sub> (on)			270		ns	
Rise Time	t <sub>r</sub>	See specified Test Circuit.		850		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)			3300		ns	
Fall Time	t <sub>f</sub>			1700		ns	
Total Gate Charge	Qg			10		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =7A		2.1		nC	
Gate-to-Drain "Miller" Charge	Qgd			2.0		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =7A, V <sub>GS</sub> =0V		0.75	1.2	V	

# Switching Time Test Circuit

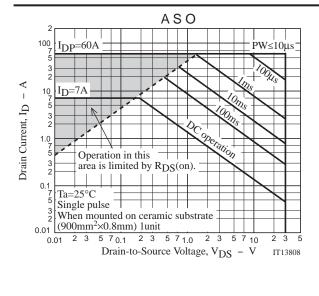


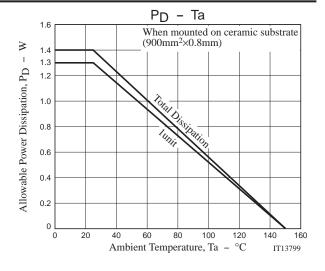
## **Ordering Information**

Device	Package Shipping		memo	
ECH8664R-TL-H	CH8664R-TL-H ECH8		Pb Free and Halogen Free	



## ECH8664R



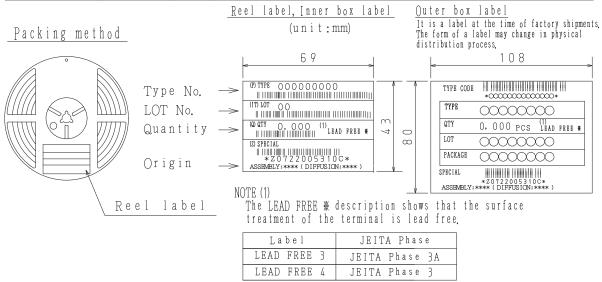


#### **Embossed Taping Specification**

#### ECH8664R-TL-H

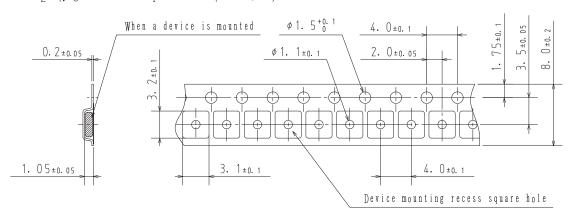
#### 1. Packing Format

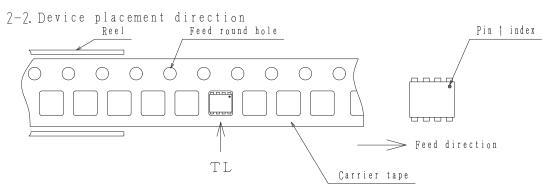
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



## 2. Taping configuration

2-1. Carrier tape size (unit:mm)





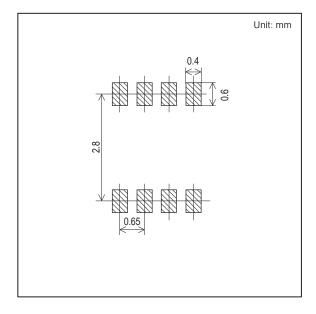
Those with pin 1 index on the feed hole side · · · · · TL

# **Outline Drawing**

ECH8664R-TL-H

# Mass (g) Unit 0.02 \* For reference mm 0. 15<sup>+0. 1</sup><sub>-0. 05</sub> 0. 25±0.06 2. 9±0.06 0~0.02 2. 8±0. 05 2. 3±0.06 LOT No. 0. 25±0.06 0. 3<sup>+0. 1</sup> 0.65 PIN#1 0. 9±0. 05 0.05 \$ \$

# Land Pattern Example



Note on usage: Since the ECH8664R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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